## AMENDMENTS TO THE SPECIFICATION

**Please replace the present title with the following amended title:**

METHOD OF FORMING A PROJECTION ELECTRODE~~, ITS FORMING METHOD AND APPARATUS FOR TESTING AN ELECTRONIC COMPONENT~~

**Please replace the second paragraph on page 9 with the following amended paragraph:**

As shown in FIG. 2A, a predetermined circuit pattern is formed (S1) by an etching process, etc., on an electroconductive material 2 on a board material such as a copper foil stacking board comprising a printed circuit board 1 of an insulating material and the electroconductive material 2, such as copper, as shown in FIG. 2B. In this case, in place of a copper foil stacking board, a metal such as Zn, Ni, Ag, Pd, Cr, Ti, Be, W, Rh, Ru, etc., or an alloy thereof or an oxide electrode material, such as indium oxide or ruthenium oxide, can be attached, as an electrode material, in the form of a foil, or plated, or formed by a thin film method, such as an evaporation method, on a proper substrate. Then, as shown in FIG. 2C, a dry film resist (hereinafter referred to as a DF) 3 formed of, for example, a photosensitive film, is stacked on the electroconductive material 2 (S2) and those portions other than projection electrode formation areas 4 formed on the wiring board's electrodes, serving as the portions of a circuit pattern, are masked with a mask 5 and exposed to light. After the removal of the mask 5, development is made, thus eliminating the DF3 (S3) other than the projection electrode formation areas 4 on the wiring board 1 as shown in FIG. 2D. FIG. 4 is a view from above, of a partially eliminated DF3 and wiring board 1 and, at the step S3, holes 31 are provided where the DF3 has been eliminated. By doing so, the DF mask portion 30 provides no isolated pattern and the problem involving peeling of the DF mask portion 30 by the etching process can never occur. It is to be noted that FIG. 2E is a cross-sectional view taken along broken line ~~A-A'~~ I-I of the wiring board 1 in FIG. 4.

**Please replace the first paragraph on page 17 with the following amended paragraph:**

As shown in FIG. 9D, which is a sectional view taken along line ~~A-A'~~ I-I in FIG. 11, the insulating layer 40 is subjected to, for example, isotropic etching, thus removing surface regions of the layer 40 which are exposed through the openings 31 (FIG. 11) of the DF 64 (Step S14). Projections 41 are thereby formed of the insulating layer 40. The isotropic etching is continued, sharpening the projections 41.